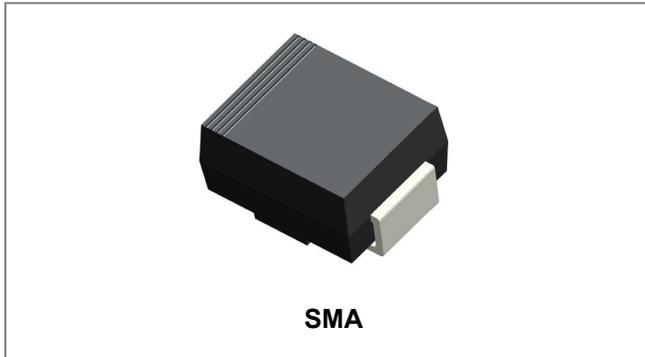


GS1A THRU GS1M

1.0A SURFACE MOUNT GLASS PASSIVATED RECTIFIER



Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-0
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: SMA molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 0.06 grams

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Characteristic	Symbol	GS1A	GS1B	GS1D	GS1G	GS1J	GS1K	GS1M	Units
Peak Repetitive Reverse Voltage	V _{RRM}								
Working Peak Reverse Voltage	V _{RWM}	50	100	200	400	600	800	1000	V
DC Blocking Voltage	V _R								
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	V
Average Rectified Output Current @T _L = 100°C	I _o	1.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	30							A
Forward Voltage @ I _F = 1.0 A	V _F	1.10							V
Peak Reverse Current @T _A = 25°C	I _{RM}	5.0							μA
At Rated DC Blocking Voltage @T _A = 125°C		200							
Reverse Recovery Time(Note1)	t _{rr}	2.5							μS
Typical Junction Capacitance(Note2)	C _J	15							pF
Typical Thermal Resistance Junction to Lead (Note 3)	R _{θJL}	30							°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +175							°C

Note: 1. Reverse recovery condition I_F=0.5A, I_R=1.0A, I_{rr}=0.25A
 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
 3. Mounted on P.C.B.with 8.0mm² land areas.

Ratings and Characteristics Curves

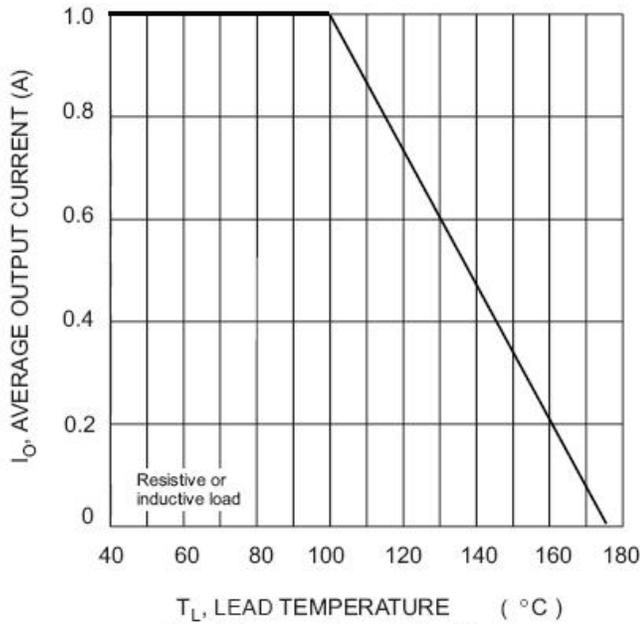


Fig. 1 Forward Current Derating Curve

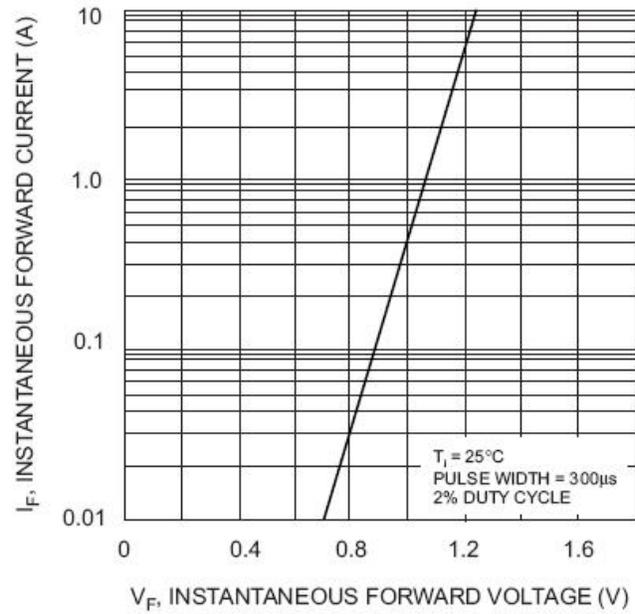


Fig. 2 Typical Forward Characteristics

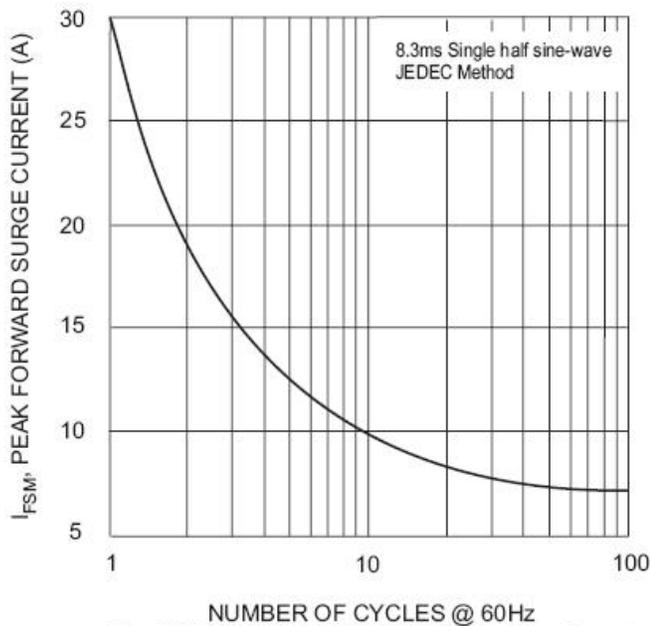


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

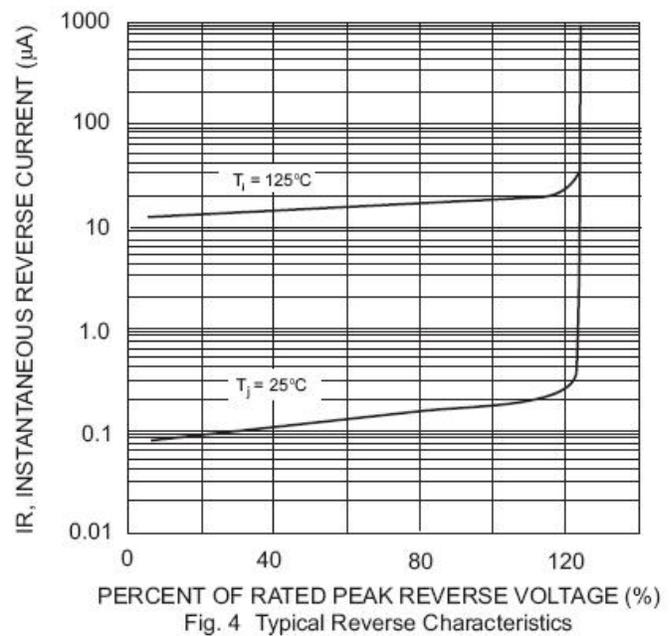
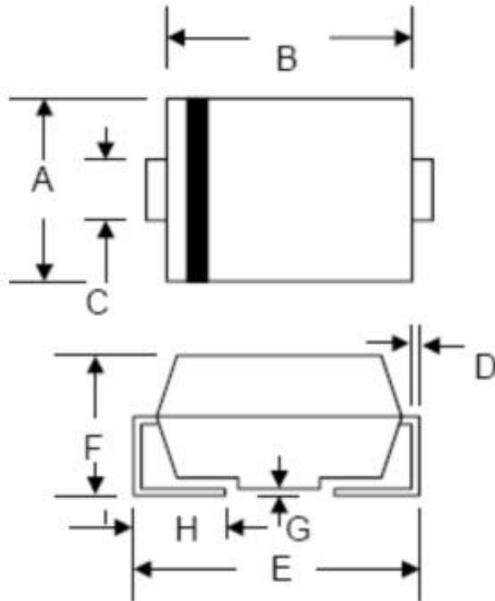


Fig. 4 Typical Reverse Characteristics

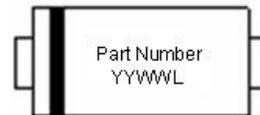
Mechanical Dimensions SMA


SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.84	0.094	0.112
B	3.99	4.75	0.157	0.187
C	1.05	1.70	0.041	0.067
D	0.15	0.51	0.006	0.020
E	4.80	5.66	0.189	0.223
F	1.90	2.95	0.075	0.116
G	0.05	0.203	0.002	0.008
H	0.76	1.52	0.030	0.600

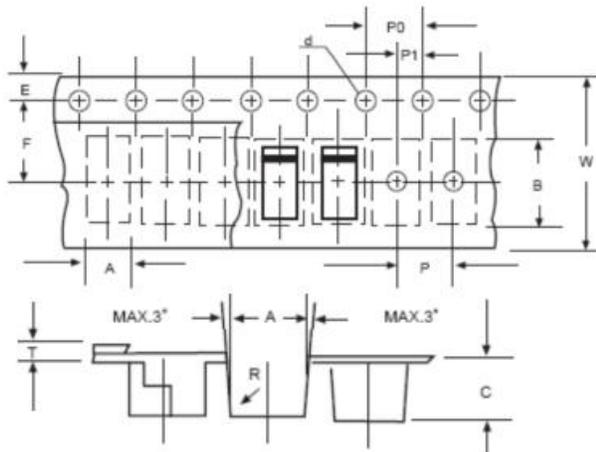
Ordering Information

Device	Package	Shipping
GS1A-GS1M	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram


First row: Part Number (GS1A, GS1B, GS1D, GS1G, GS1J, GS1K, GS1M)
 Second row: YYWWL
 YY is the manufacture year,
 WW is the manufacture week code,
 L is the wafer's Lot Number

Carrier Tape Specification SMA


SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

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